

isc Triacs

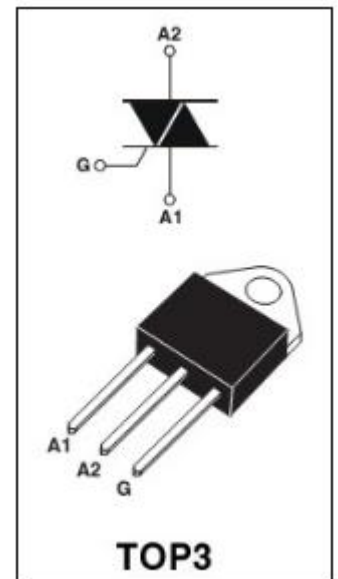
TPDV1240RG

FEATURES

- With TOP3 insulated package
- Be suitable for general purpose where high surge current capability is required.
Application such as phase control and tatic switching on inductive or resistive load.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	1200	V
V_{RRM}	Repetitive peak reverse voltage	1200	V
$I_{T(RMS)}$	RMS on-state current (full sine wave)Tc=75°C	40	A
I_{TSM}	Non-repetitive peak on-state current $t_p=10ms$	350	A
T_j	Operating junction temperature	-40~125	°C
T_{stg}	Storage temperature	-40~150	°C
$P_{G(AV)}$	Average gate power dissipation($T_j=125^{\circ}C$)	1	W
$R_{th(j-c)}$	Thermal resistance, junction to case	1.2	°C/W
$R_{th(j-a)}$	Thermal resistance, junction to ambient	50	°C/W



ELECTRICAL CHARACTERISTICS (Tc=25°C unless otherwise specified)

SYMBOL	PARAMETER		CONDITIONS	MAX	UNIT
I_{RRM}	Repetitive peak reverse current		$V_R=V_{RRM}$, $V_R=V_{RRM}$, $T_j=125^{\circ}C$	0.02 8	mA
I_{DRM}	Repetitive peak off-state current		$V_D=V_{DRM}$, $V_D=V_{DRM}$, $T_j=125^{\circ}C$	0.02 8	mA
I_{GT}	Gate trigger current	I	$V_D=12V$; $R_L=33\Omega$	200	mA
		II		200	
		III		200	
I_H	Holding current		$I_{GT}=0.5A$, Gate Open	50	mA
V_{GT}	Gate trigger voltage all quadrant		$V_D=12V$; $R_L=33\Omega$	1.5	V
V_{TM}	On-state voltage		$I_{TM}=35A$; $t_p=380\mu s$	1.8	V